## **AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

## **LISTING OF CLAIMS:**

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 (Currently Amended) An optical semiconductor device comprising:

an optical semiconductor element having first and second electrodes;

a first conductor line connected to one-the first electrode of a pair of electrodes of the optical semiconductor element, and supplying an a first electric signal to the optical semiconductor element;

a second conductor line connected to the <u>other-second</u> electrode <u>of the</u>

<u>pair of electrodes</u> of the optical semiconductor element, and supplying <u>an a</u>

<u>second</u> electric signal to the optical semiconductor element;

a first inductance element connected to the one-first electrode of the optical semiconductor element and the first conductor line; and

a second inductance element connected to <u>between</u> the <u>other-second</u> electrode of the optical semiconductor element <u>and a ground potential</u>, and <u>connected to</u> the second conductor line, wherein

the first and the second conductor lines constitute a pair of differential lines.

2. (Currently Amended) The optical semiconductor device according to claim 1, further comprising a pair of matching resistors connected

to the <u>one-first and second</u> electrodes <u>and the other electrode</u> of the optical semiconductor element, respectively, and introducing the <u>first and second</u> electric signals to the optical semiconductor element, <u>respectively</u>.

3. (Original) The optical semiconductor device according to claim 2, comprising:

a first bias circuit including the first inductance element and a first resistor connected in parallel to the first inductance element; and a second bias circuit including the second inductance element and a second resistor connected in parallel to the second inductance element.

4. (Original) The optical semiconductor device according to claim 1, comprising:

a first bias circuit including the first inductance element and a first resistor connected in parallel to the first inductance element; and a second bias circuit including the second inductance element and a second resistor connected in parallel to the second inductance element.

- 5. (Currently Amended) The optical semiconductor device according to claim 1 claim 2, comprising a filter that cuts off frequencies higher than at least a maximum repetition frequency of a digital signal, the filter provided between the first and the second conductor lines and the pair of matching resistors.
  - 6. (Original) The optical semiconductor device according to claim 5,

## wherein

the filter includes a first conductor finger section and a second conductor finger section in which a plurality of conductors crossing the first and the second conductor lines are formed, respectively, to have a comb shape, the first conductor finger section and the second conductor finger sections being alternately arranged.

7. (Currently Amended) The optical semiconductor device according to claim 6, comprising:

a package containing therein the first and the second conductor lines therein;

a lens that condenses [[a]] light emitted from the optical semiconductor element; and

an optical fiber holding member that holds an optical fiber.

- 8. (Original) The optical semiconductor device according to claim 7, wherein the first and the second inductance elements are air-cored coils.
- 9. (Original) The optical semiconductor device according to claim 8, wherein the optical semiconductor element is a semiconductor laser diode.
- 10. (Currently Amended) The optical semiconductor device according to claim 1, comprising:

a package containing therein the first and the second conductor lines therein;

a lens that condenses [[a]] light emitted from the optical semiconductor element; and

an optical fiber holding member that holds an optical fiber.

- 11. (Original) The optical semiconductor device according to claim 1, wherein the first and the second inductance elements are air-cored coils.
- 12. (Original) The optical semiconductor device according to claim 1, wherein the optical semiconductor element is a semiconductor laser diode.
- 13. (Currently Amended) The optical semiconductor device according to claim 1, wherein impedances of at least two bias circuits are set to be substantially asymmetric.
- 14. (Currently Amended) An optical semiconductor device comprising:

an optical semiconductor element having first and second electrodes;

a first differential input terminal supplying an <u>a first</u> electric signal to <del>one</del> of a pair of electrodes the first electrode of the optical semiconductor element;

a second differential input terminal supplying an <u>a second</u> electric signal opposite in phase to the <u>first</u> electric signal supplied by the first differential input terminal, to the <u>other second</u> electrode of the pair of electrodes of the optical semiconductor element;

a first inductance element connected to the one-first electrode of the

optical semiconductor element and the first conductor line, and cutting off the <u>first</u> electric signal at a high frequency; and

a second inductance element connected to between the other second electrode of the optical semiconductor element and a ground potential, and connected to the second conductor line, and cutting off the second electric signal at a high frequency.

15. (Currently Amended) An optical semiconductor device comprising:

an optical semiconductor element <u>having first and second electrodes</u>; a pair of differential amplifiers each having <u>one a first</u> terminal and <u>the other a second</u> terminal connected to <u>one electrode and the other electrode of a pair of the first and second electrodes of the optical semiconductor element, respectively, and <u>each</u> supplying <u>an first and second electric signals</u> to the optical semiconductor element, respectively;</u>

a first inductance element connected to the one-first electrode of the optical semiconductor element, and cutting off the first electric signal at a high frequency; and

a second inductance element connected to between the other second electrode of the optical semiconductor element and a ground potential, and cutting off the second electric signal at a high frequency.

16. (Currently Amended) An optical semiconductor device comprising:

an optical semiconductor element having first and second electrodes; first and second conductor lines connected to a pair of the first and second electrodes of the optical semiconductor element, and supplying first and second differential signals to the optical semiconductor element, respectively;

a first terminal electrically connected to the first conductor line and one the first electrode of the pair of electrodes of the optical semiconductor element; and

a second terminal electrically connected to the second conductor line and the other second electrode of the optical semiconductor element; wherein

a first bias circuit electrically connected to the first terminal and cutting off the first differential signal at a high frequency; and

a second bias circuit electrically connected to the second terminal, between the second electrode of the optical semiconductor element and a ground potential, and cutting off the second differential signal at a high frequency.

the first and the second terminals are connected to bias circuits that cut off high frequencies, respectively.

17. (Currently Amended) An optical semiconductor device comprising:

an optical semiconductor element having first and second electrodes; a first conductor line having one end connected to one of a pair of

electrodes the first electrode of the optical semiconductor element, and supplying an <u>a first</u> electric signal to the optical semiconductor element;

a second conductor line having one end-connected to the other second electrode of the pair of electrodes of the optical semiconductor element, and supplying an a second electric signal to the optical semiconductor element;

a first inductance element connected to the ene-first electrode of the optical semiconductor element and the first conductor line; and

a second inductance element connected to between the other second electrode of the optical semiconductor element and a ground potential, and connected to the second conductor line, wherein

the optical semiconductor element is driven by a push-pull operation.

- 18. (Currently Amended) The optical semiconductor device according to claim 17, wherein impedances of at least two bias circuits are set to be substantially asymmetric.
- 19. (New) The optical semiconductor device according to claim 1, further comprising:

a first matching resistance connected in parallel to the first electrode of the optical semiconductor element, and introducing the first electric signal to the optical semiconductor element; and

a second matching resistance connected in parallel to the second electrode of the optical semiconductor element, and introducing the second electric signal to the optical semiconductor element.

- 20. (New) The optical semiconductor device according to claim 19, further comprising a filter circuit that cuts off frequencies higher than at least a maximum repetition frequency of a digital signal, the filter having first and second electrodes respectively connected to the first and second matching resistances.
- 21. (New) The optical semiconductor device according to claim 1, wherein:

the first inductance element is connected in parallel to the first conductor line and the first electrode of the optical semiconductor element; and

the second inductance element is connected in parallel to the second conductor line and the second electrode of the optical semiconductor element.

- 22. (New) The optical semiconductor device according to claim 1, wherein the first inductance element is connected between the first electrode of the optical semiconductor element and a current source.
- 23. (New) The optical semiconductor device according to claim 12, wherein the first electrode is a cathode of the semiconductor laser diode, and the second electrode is an anode of the semiconductor laser diode.